## Et-304/EEtE/3rd Sem/2018/M

## ELEMENTS OF ELECTRONICS ENGINEERING

Full Marks - 70

Time - Three hours

The figures in the margin indicate full marks for the questions.

## FIRST PART

Marks - 25

| 1. Fi | ll in | the | bla | anks | : |
|-------|-------|-----|-----|------|---|
|-------|-------|-----|-----|------|---|

1×15=15

- (i) The electrode of a tube from where the electrons are emitted is called ———.
- (ii) In vacuum tubes emission is used.
- (iii) An electronic device that converts AC into DC is called a ———.

| (iv) A vacuum diode conducts only when plate is —— w.r.t. cathode.                            |
|---|
| (v) For half wave rectification — vacuum diode is needed.                                     |
| (vi) Tube used for amplification must have — grid.  |
| (vii) For faithful amplification, the control grid must be kept at — potential w.r.t cathode. |
| (viii) A semiconductor has a — temperature co-efficient of resistance.                        |
| (ix) In a transistor, base is made very —   |
| (x) Class — power amplifier has the highest collector efficiency.                             |
| (xi) The last stage of an audio amplifier is called   |
| (xii) A capacitor circuit does not allow passing components.                                  |
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- (xiii) Negative feedback in an amplifier increases the ——— of its voltage gain.
- (xiv) To obtain undamped oscillations ———
  feedback is necessary.
- (xv) In a transistor, ——— is made most highly doped section.
- 2. Select the correct answers in the following :  $1 \times 5 = 5$ 
  - (i) In an NPN transistor with normal bias
    - (a) Only holes cross the collector junction
    - (b) Only majority carriers cross the collector junction.
    - (c) The emitter resistance has a high resistance.
    - (d) The emitter junction is forward biased and collector junction is reverse biased.

- (ii) The silicon transistors are more widely used than germanium transistors because
  - (a) They have smaller leakage current
  - (b) They have better ability to dissipate heat.
  - (c) They have smaller depletion layers.
  - (d) They have larger current carrying capacity.
- (iii) The maximum efficiency of class B amplifier is
  - (a) 50%

(b) 78.5%

(c) 35%

- (d) 100%
- (iv) In push-pull amplifiers, usually biasing is not required because
  - (a) DC battery V<sub>CC</sub> is employed
  - (b) Power transistors do not require biasing
  - (c) Heat sink is used with the transistors
  - (d) Transistors are working in class B operation.

- (v) An oscillator is a
  - (a) Rotating device
  - (b) Static electronic device
  - (c) Rotating electronic device
  - (d) Electro-mechanical device
- 3. State true or false:

1×5=5

- (i) To be a good emitter the cathode material should have low work function.
- (ii) In a transistor, there are three PN junctions.
- (iii) When PN junction is forward biased, it offers low resistance and larger current flows through it.
- (iv) In transistor circuit,  $I_E = I_B + \beta I_B$
- (v) Avalanche breakdown in a crystal diode occurs when reverse bias exceeds a certain value.